General Description

The WSD4070DN is the highest performance trench N-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSD4070DN meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

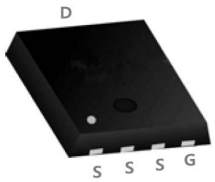
Product Summery

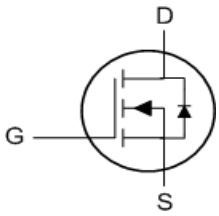
BVDSS	RDSON	ID
40V	4.5mΩ	68A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN3.3X3.3-EP Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[G]	68	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[G]	35	A
I_{DM}@T_C=25℃	Pulsed Drain Current[C]	144	A
EAS	Avalanche Energy ,Single Pulse (L=0.3mH)	80	mJ
I_{AS}	Avalanche Current	40	A
P_D@T_A=25℃	Total Power Dissipation[A]	3.1	W
P_D@T_A=70℃	Total Power Dissipation[A]	2.0	W
T_J T_{STG}	Storage and Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [A]	---	60	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[A]	---	2.8	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=7A	---	4.5	5.5	mΩ
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V , I_D=5A	---	5.3	7.6	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.3	1.9	2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-6.	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V , T_J=25℃	---	-	2	uA
		V_{DS}=40V , V_{GS}=0V , T_J=55℃	---	-	10	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	-	±100	nA
gfs	orward Transconductance	V_{DS}=5V , I_D=20A	---	67	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.8	1.5	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=20V, V_{GS}=10V, I_{DS}=20A	---	28	---	nC
Q_{gs}	Gate-Source Charge		---	3.9	---	
Q_{gd}	Gate-Drain Charge		---	6.0	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=20V, R_L=1Ω , V_{GS}=10V, R_G=3Ω.	---	7.2	---	ns
T_r	Rise Time		---	3.0	---	
$T_{d(off)}$	Turn-Off Delay Time		---	23	---	
T_f	Fall Time		---	3.5	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	2820	---	pF
C_{oss}	Output Capacitance		---	220	---	
C_{rss}	Reverse Transfer Capacitance		---	150	---	

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25℃. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t ≤ 10s value and the maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design, and the maximum temperature of 150℃ may be u sed if the PCB allows it.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150℃, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150℃. Ratings are based on low frequency and duty cycles to keep initial T_J =25℃.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150℃. The SOA curve provides a single pulse ratin g.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25℃.

Typical Operating Characteristics

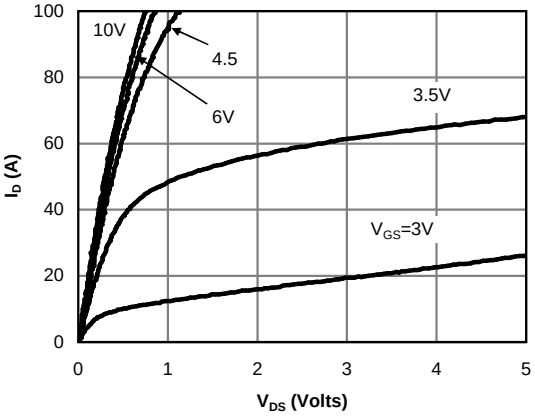


Fig 1: On-Region Characteristics (Note E)

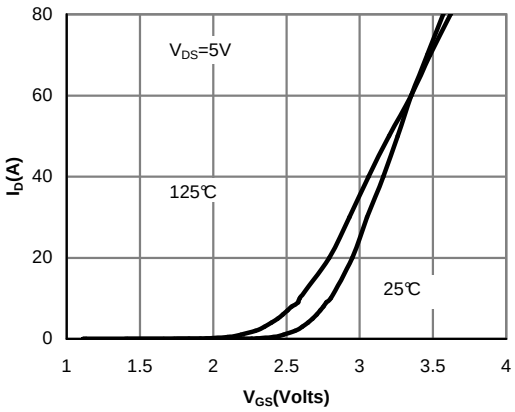


Figure 2: Transfer Characteristics (Note E)

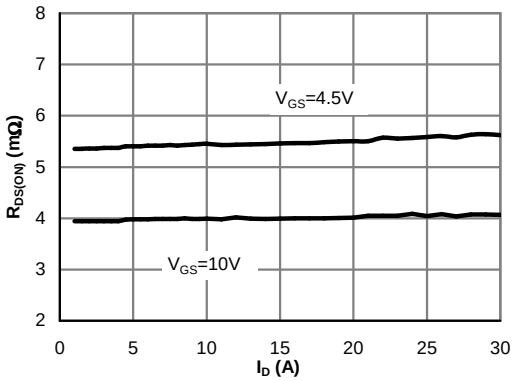


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

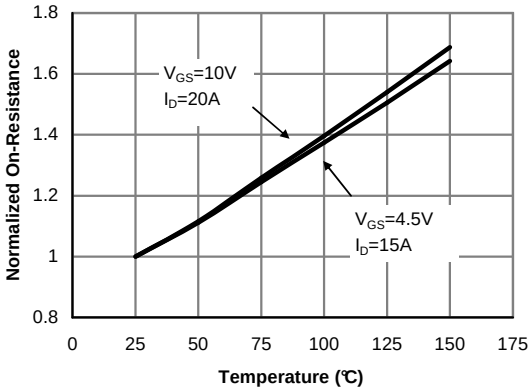


Figure 4: On-Resistance vs. Junction Temperature (Note E)

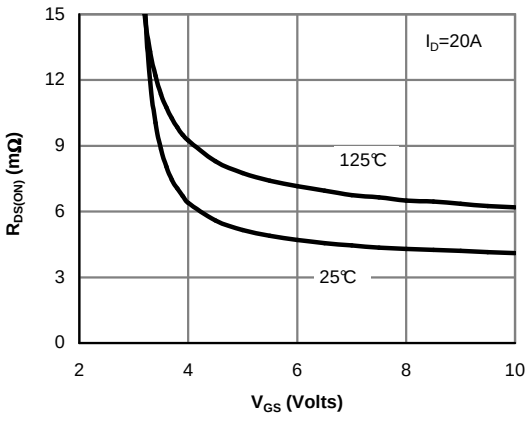


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

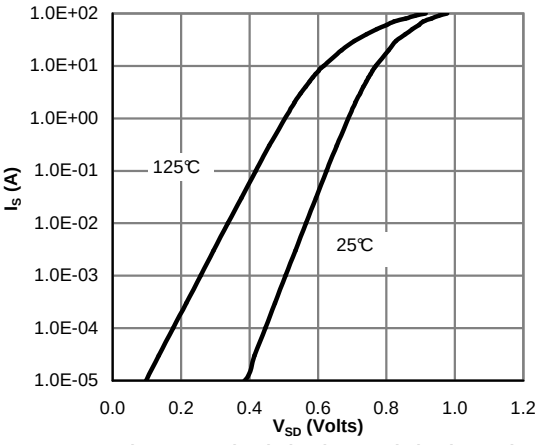


Figure 6: Body-Diode Characteristics (Note E)

Typical Operating Characteristics (Cont.)

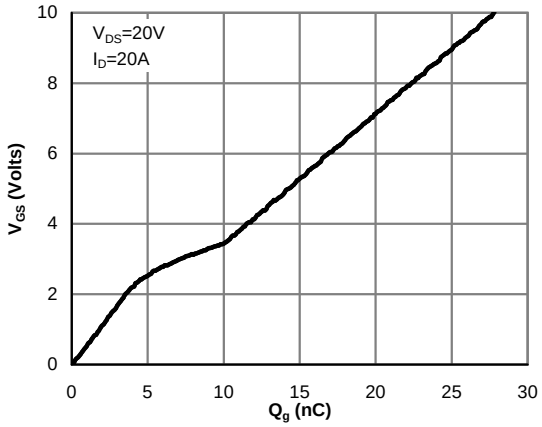


Figure 7: Gate-Charge Characteristics

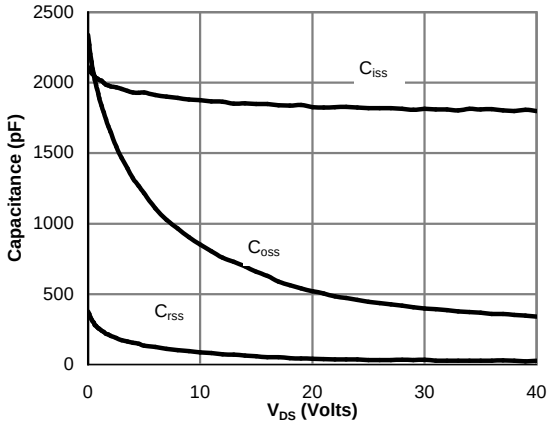


Figure 8: Capacitance Characteristics

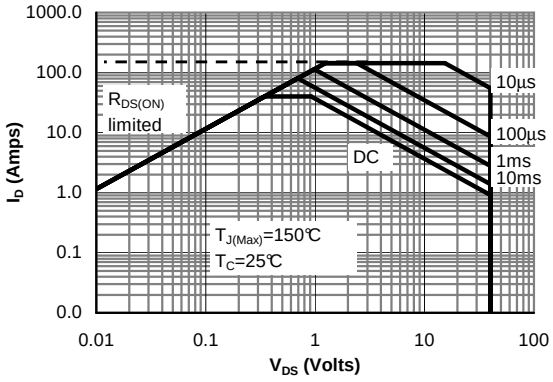


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

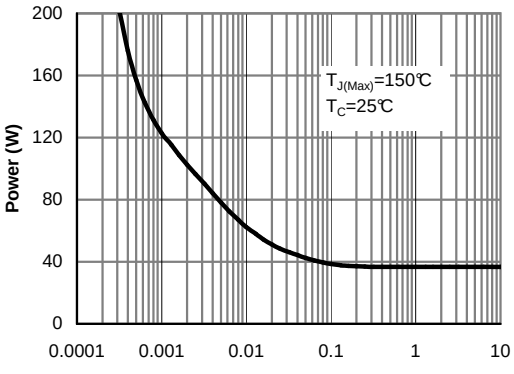


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

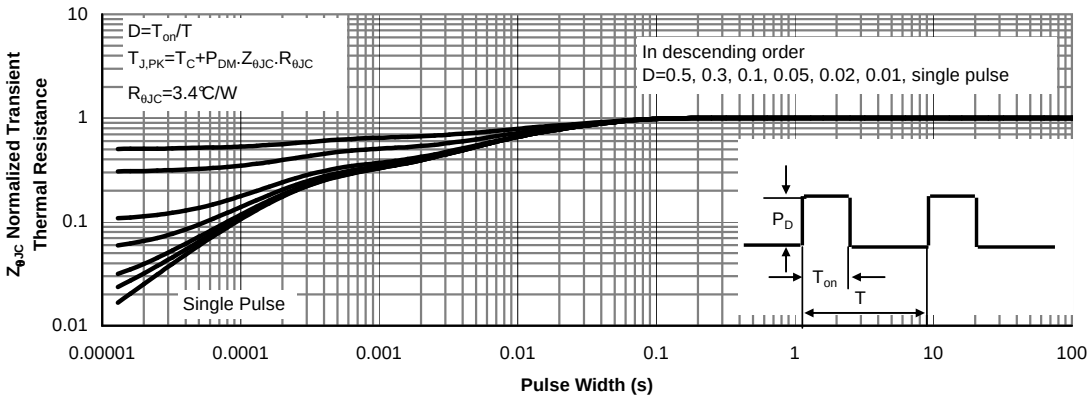


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Typical Operating Characteristics (Cont.)

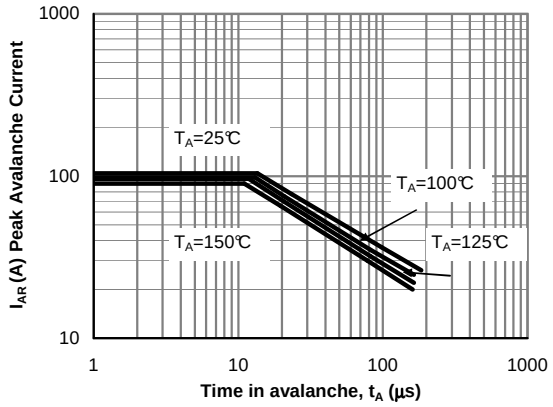


Figure 12: Single Pulse Avalanche capability (Note C)

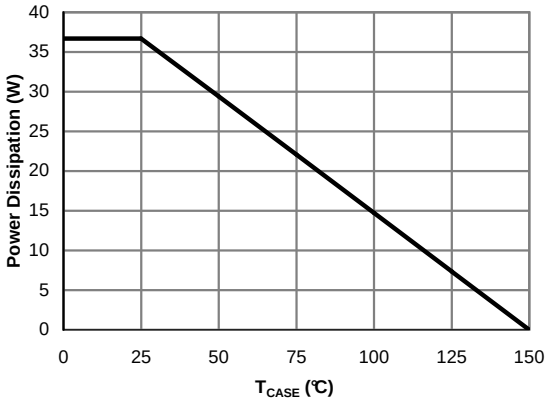


Figure 13: Power De-rating (Note F)

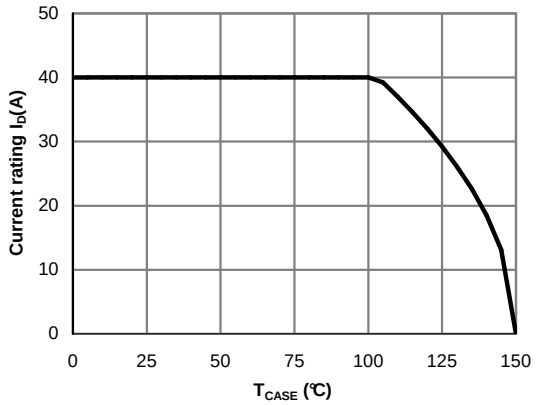


Figure 14: Current De-rating (Note F)

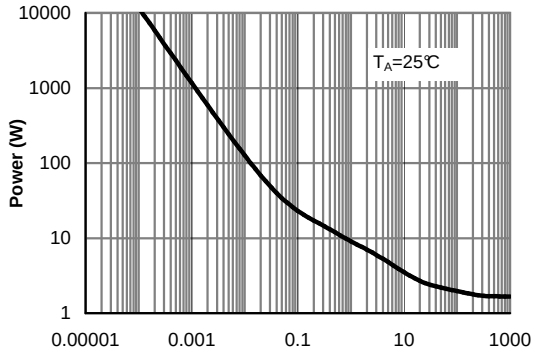


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

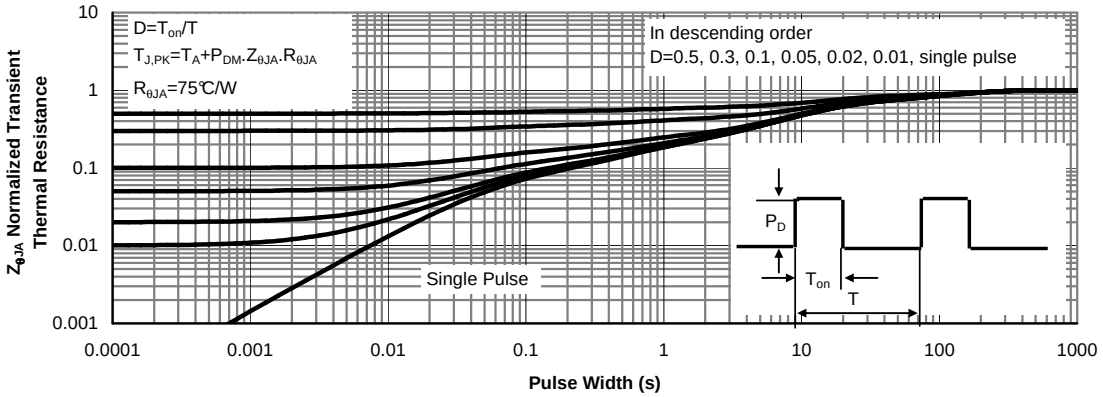
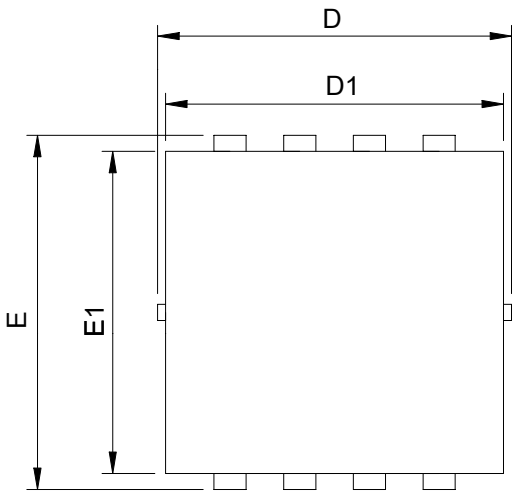
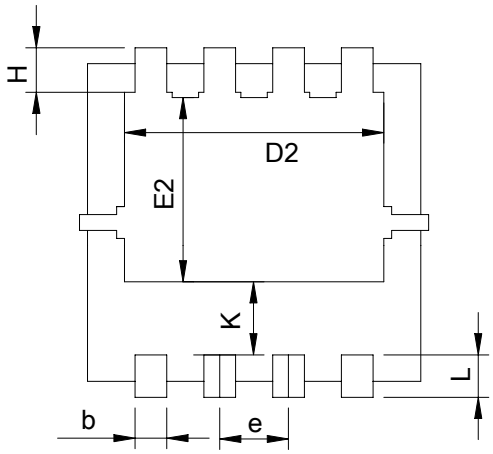


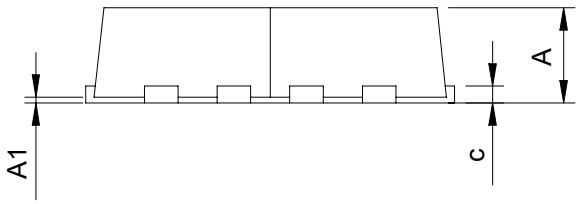
Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)



Top View

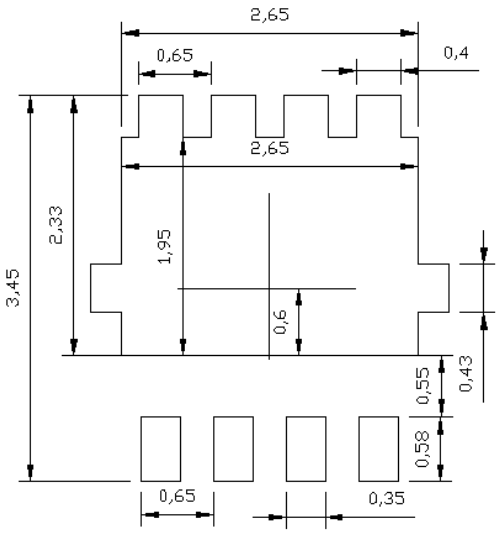


Bottom View



Side View

SYMBOL	DFN3.3x3.3_EP			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022



UNIT: mm

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